

Search History (5 pp.) ~~9/7/05~~ (9/7/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
L8	2	silicon adj germanium near4 band adj gap near4 wide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
L9	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:12
L10	37	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:14
L11	10	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:20
L12	4900	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/07 16:20
L13	139	12 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
L14	16	12 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4) and (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S1	4	"264914".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/20 09:44
S2	6	"760087".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26

S3	3	("6808971").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S4	1	"6429085".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:27
S5	1	"5006913".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:42
S6	1	"4768076".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:43
S7	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:44
S8	8	((("4692994") or ("4768076") or ("5006913") or ("6429085"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 07:44
S9	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2005/09/07 07:45
S10	0	battacharyya.in. and strained and (sige gesi si-ge ge-si silicon adj germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S11	0	battacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S12	644	bhattacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S13	73	bhattacharyya.in. and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S14	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:57
S15	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:58

S16	35	bhattacharyya.in. and cmos and (thin adj film TFT) and strained. clm. and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:17
S17	11	(inverter invertor).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:24
S18	11	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S19	34	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S20	5	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and @ad<"20020311"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 10:33
S21	2	("5298452"):PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:46
S22	191	speed near4 CMOS near4 (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:47

S23	1	improve near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:49
S24	44	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 11:06
S25	49	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:09
S26	14	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter) and (single adj crystal monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:08
S27	23	"6251751"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:41
S28	18	S27 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S29	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S30	1	S29 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:19
S31	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S32	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22

S33	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:25
S34	28	polycrystalline near4 silicon adj germanium near10 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:26
S35	8	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S36	1	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27